

Exciton binding energy in quantum wells

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Citation Report

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1	Binding energy of biexcitons and bound excitons in quantum wells. <i>Physical Review B</i> , 1983, 28, 871-879.	1.1	265
2	Variational calculations on a quantum well in an electric field. <i>Physical Review B</i> , 1983, 28, 3241-3245.	1.1	740
3	Binding energy for the surface biexcitonic positive ion. <i>Journal of Physics C: Solid State Physics</i> , 1983, 16, 5723-5728.	1.5	24
4	Eigenstates of Wannier excitons near a semiconductor surface. <i>Physical Review B</i> , 1983, 28, 4585-4592.	1.1	65
5	Raman Scattering Resonant with Quasi-Two-Dimensional Excitons in Semiconductor Quantum Wells. <i>Physical Review Letters</i> , 1983, 51, 1293-1296.	2.9	122
6	Wannier exciton in quantum wells. <i>Physical Review B</i> , 1983, 28, 4878-4881.	1.1	147
7	Wannier excitons in GaAs-Ga $_{1-x}$ Al $_x$ As quantum-well structures: Influence of the effective-mass mismatch. <i>Physical Review B</i> , 1984, 30, 7302-7304.	1.1	69
8	A Wannier Exciton in a Quantum Well: Subband Dependence. <i>Journal of the Physical Society of Japan</i> , 1984, 53, 3138-3145.	0.7	50
9	Spectrum of two-dimensional excitons in heterojunction superlattices. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1984, 101, 158-160.	0.9	4
10	An alternative approach to exciton binding energy in a GaAs-Al $_x$ Ga $_{1-x}$ as quantum well. <i>Solid State Communications</i> , 1984, 50, 589-593.	0.9	61
11	Picosecond time-resolved study of excitons in GaAs-AlAs multi-quantum-well structures. <i>Physical Review B</i> , 1984, 29, 2324-2327.	1.1	103
12	Solid-state perspectives of the photoelectrochemistry of semiconductor-electrolyte junctions. <i>Nature</i> , 1984, 312, 21-27.	13.7	104
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14	Hydrogenic impurity states in quantum-well wires. <i>Physical Review B</i> , 1984, 29, 6632-6639.	1.1	206
15	Band-Edge Electroabsorption in Quantum Well Structures: The Quantum-Confined Stark Effect. <i>Physical Review Letters</i> , 1984, 53, 2173-2176.	2.9	1,558
16	Sharp-line photoluminescence spectra from GaAs-GaAlAs multiple-quantum-well structures. <i>Physical Review B</i> , 1984, 29, 7038-7041.	1.1	80
17	Energy levels of Wannier excitons in GaAs-Ga $_{1-x}$ Al $_x$ As quantum-well structures. <i>Physical Review B</i> , 1984, 29, 1807-1812.	1.1	555
18	Magneto-optical determination of exciton binding energy in GaAs-Ga $_{1-x}$ Al $_x$ As quantum wells. <i>Physical Review B</i> , 1984, 30, 2253-2256.	1.1	264

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31	Hydrogenic impurity states in GaAs-Ga _{1-x} Al _x As quantum well structures. Journal of Physics C: Solid State Physics, 1985, 18, 691-700.	1.5	15
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38	Localization and homogeneous dephasing relaxation of quasi-two-dimensional excitons in quantum-well heterostructures. <i>Physical Review B</i> , 1985, 32, 7013-7015.	1.1	97
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54	Electronic states in semiconductor heterostructures. <i>IEEE Journal of Quantum Electronics</i> , 1986, 22, 1625-1644.	1.0	483

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56	Excitons in semimagnetic semiconductor quantum-well systems: Magnetic polaron effects. <i>Physical Review B</i> , 1986, 34, 1080-1084.	1.1	43
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